

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCXR162646FT

Low-Voltage 16-Bit Bus Transceiver/Register with 3.6-V Tolerant Inputs and Outputs

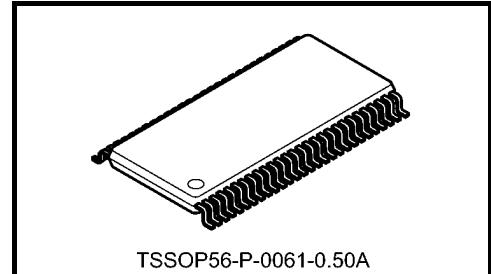
The TC74VCXR162646FT is a high-performance CMOS 16-bit bus transceiver/register. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.25 g (typ.)

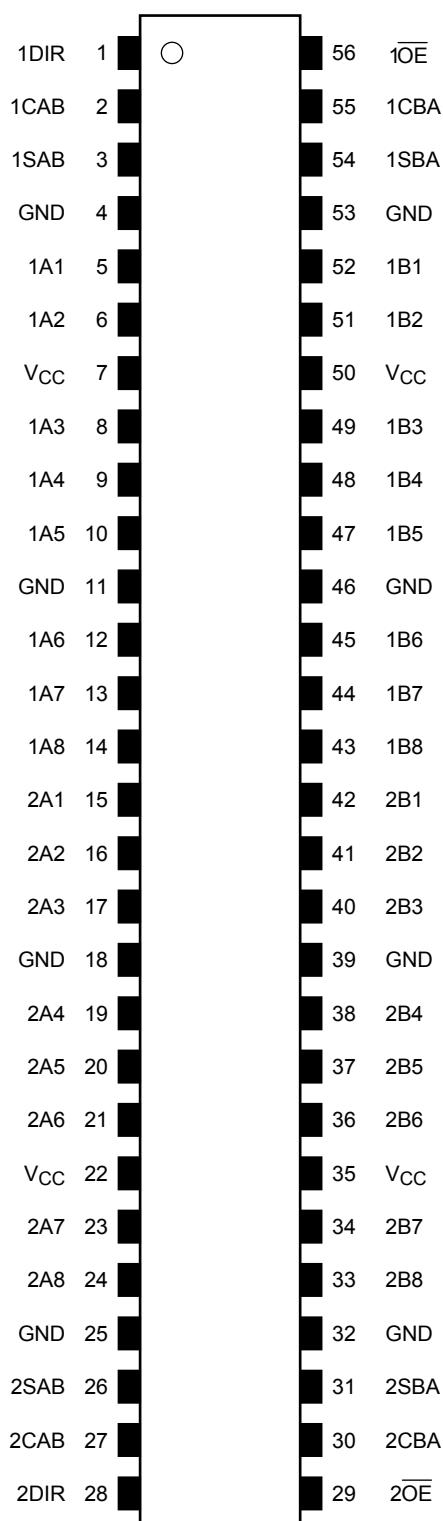
Features (Note)

- 26- Ω series resistors on outputs
- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation : $t_{pd} = 3.8$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 : $t_{pd} = 4.9$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 : $t_{pd} = 9.8$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 12$ mA (min) ($V_{CC} = 3.0$ V)
 : $I_{OH}/I_{OL} = \pm 8$ mA (min) ($V_{CC} = 2.3$ V)
 : $I_{OH}/I_{OL} = \pm 4$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200$ V
 Human body model $\geq \pm 2000$ V
- Package: TSSOP
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

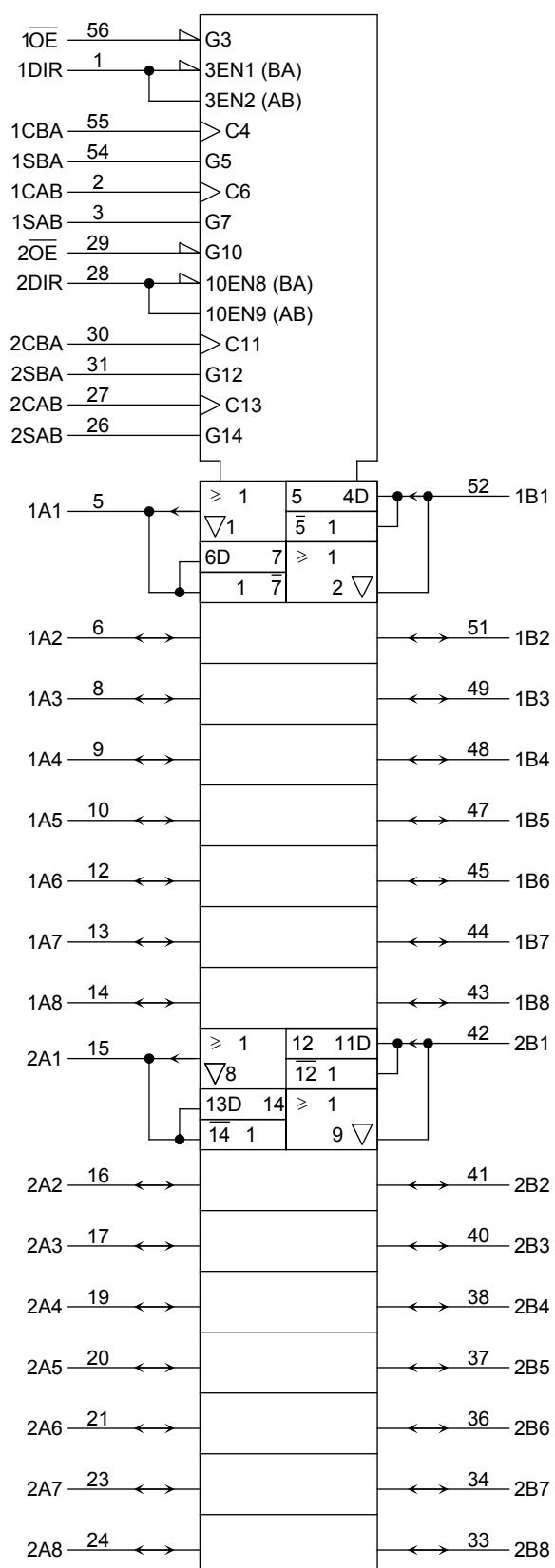
Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Control Inputs						Bus		Function
\overline{OE}	DIR	CAB	CBA	SAB	SBA	A	B	
H	X	X*	X*	X	X	Input	Input	The output functions of A and B Busses are disabled.
						Z	Z	
				X	X	X	X	Both A and B Busses are used as inputs to the internal flip-flops. Data on the Bus will be stored on the rising edge of the Clock.
L	H	X*	X*	L	X	Input	Output	The data on the A bus are displayed on the B bus.
						L	L	
						H	H	
			X*	L	X	L	L	The data on the A bus are displayed on the B Bus, and are stored into the A storage flip-flops on the rising edge of CAB.
						H	H	
	L	X*	X*	H	X	X	Qn	The data in the A storage flop-flops are displayed on the B Bus.
			X*	H	X	L	L	The data on the A Bus are stored into the A storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B Bus.
						H	H	
		X*	X*	X	L	Output	Input	The data on the B Bus are displayed on the A bus.
						L	L	
	L	X*		X	L	H	H	The data on the B Bus are displayed on the A Bus, and are stored into the B storage flip-flops on the rising edge of CBA.
						L	L	
		X*	X*	X	H	Qn	X	The data in the B storage flop-flops are displayed on the A Bus.
		X*		X	H	L	L	The data on the B Bus are stored into the B storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A Bus.
						H	H	

X: Don't care

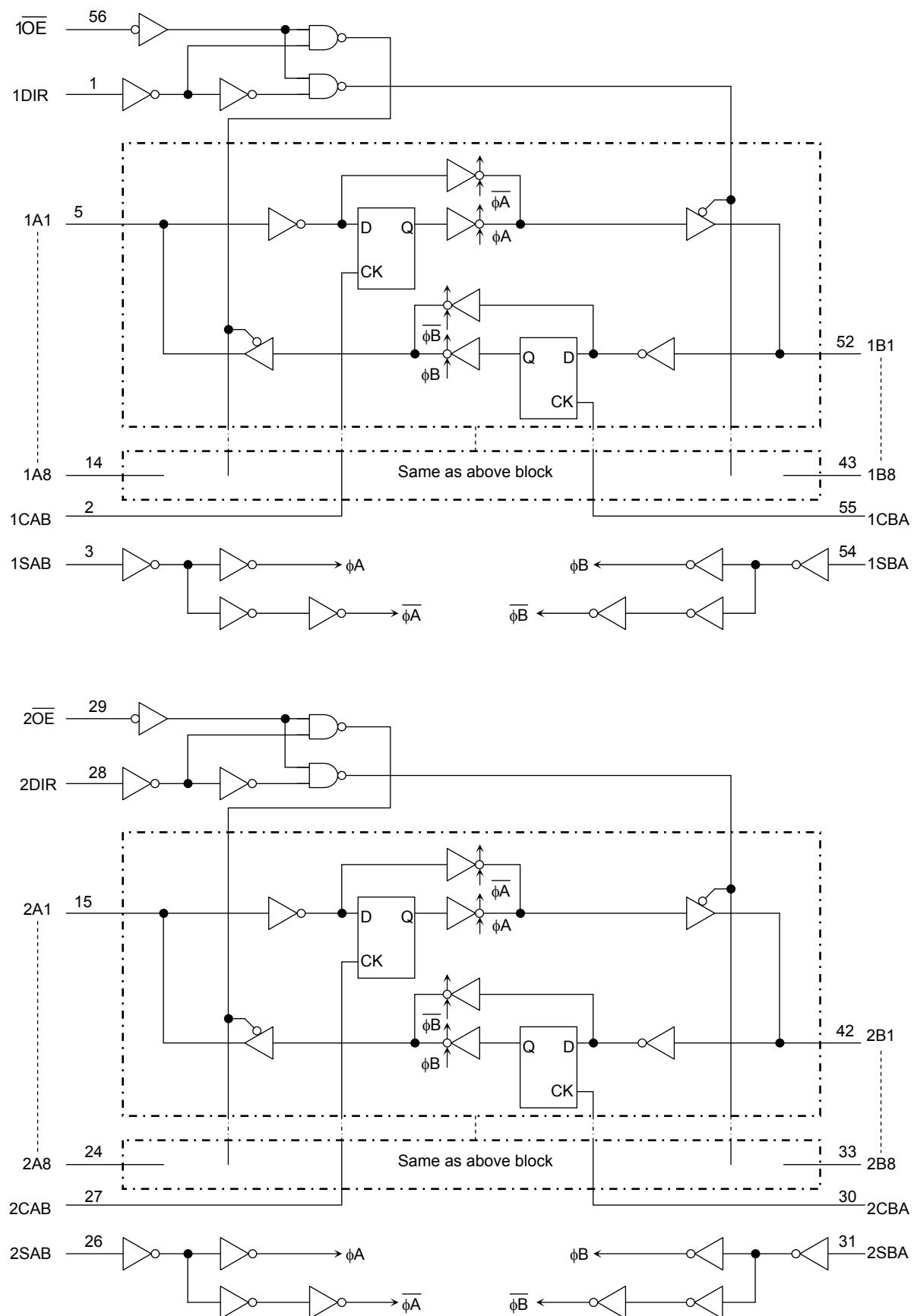
Z: High impedance

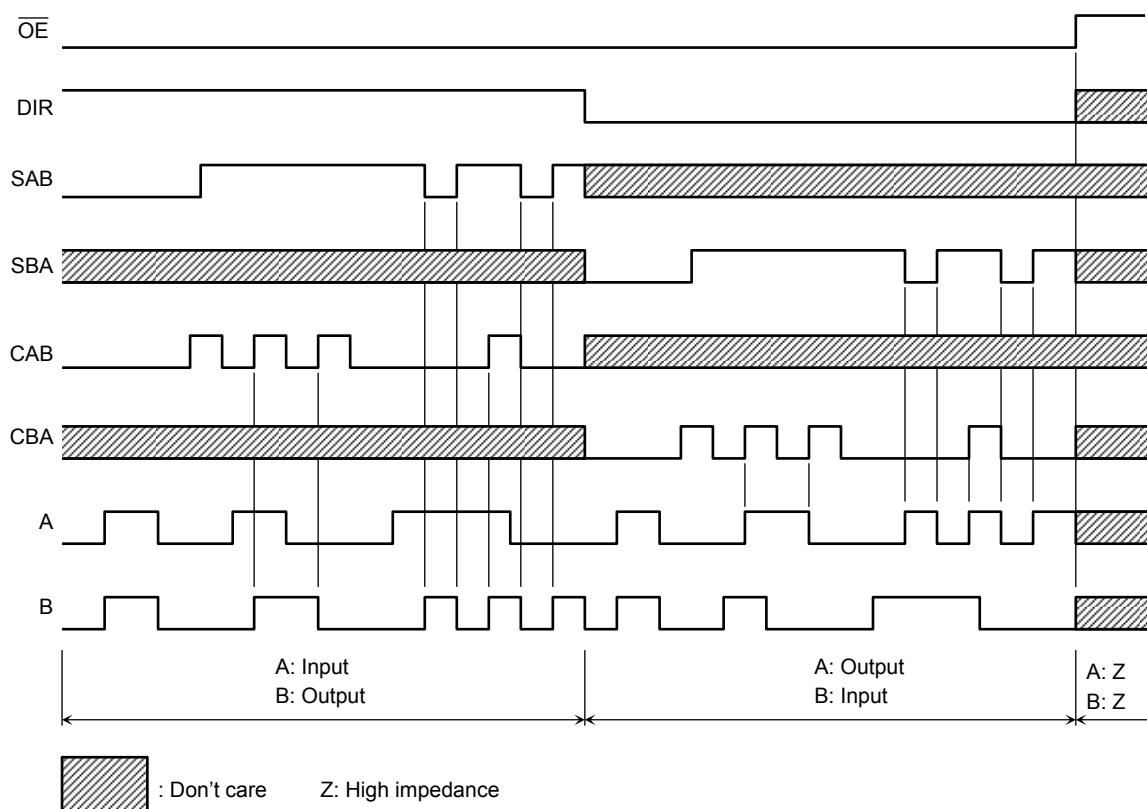
Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

*: The clocks are not internally with either \overline{OE} or DIR.

Therefore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

System Diagram



Timing Chart

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage (DIR, \overline{OE} , CAB, CBA, SAB, SBA)	V _{IN}	-0.5 to 4.6	V
DC bus I/O voltage	V _{I/O}	-0.5 to 4.6 (Note 2)	V
		-0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	\pm 50 (Note 4)	mA
DC output current	I _{OUT}	\pm 50	mA
Power dissipation	P _D	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	\pm 100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 2: OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 2)	
Input voltage (DIR, \overline{OE} , CAB, CBA, SAB, SBA)	V _{IN}	-0.3 to 3.6	V
Bus I/O voltage	V _{I/O}	0 to 3.6 (Note 3)	V
		0 to V _{CC} (Note 4)	
Output current	I _{OH} /I _{OL}	\pm 12 (Note 5)	mA
		\pm 8 (Note 6)	
		\pm 4 (Note 7)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either V_{CC} or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: V_{CC} = 3.0 to 3.6 V

Note 6: V_{CC} = 2.3 to 2.7 V

Note 7: V_{CC} = 1.8 V

Note 8: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.7 to 3.6					
	L-level	V _{IL}	—	2.7 to 3.6	—	0.8	—		
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V	
				I _{OH} = -6 mA	2.7	2.2	—		
				I _{OH} = -8 mA	3.0	2.4	—		
				I _{OH} = -12 mA	3.0	2.2	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2		
				I _{OL} = 6 mA	2.7	—	0.4		
				I _{OL} = 8 mA	3.0	—	0.55		
				I _{OL} = 12 mA	3.0	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	20.0	μA	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750		

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ V_{CC} ≤ 2.7 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit	
Input voltage	H-level		—	2.3 to 2.7					
	L-level	V _{IL}	—	2.3 to 2.7	—	—	0.7		
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V	
				I _{OH} = -4 mA	2.3	2.0	—		
				I _{OH} = -6 mA	2.3	1.8	—		
				I _{OH} = -8 mA	2.3	1.7	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2		
				I _{OL} = 6 mA	2.3	—	0.4		
				I _{OL} = 8 mA	2.3	—	0.6		
				I _{OL} = 12 mA	2.3 to 2.7	—	0.8		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	20.0	μA	

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \text{ V} \leq V_{CC} < 2.3 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level		—	1.8 to 2.3					
	L-level	V_{IL}	—	1.8 to 2.3	—	—	$0.2 \times V_{CC}$		
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.8	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -4 \text{ mA}$	1.8	1.4	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.8	—	0.2		
				$I_{OL} = 4 \text{ mA}$	1.8	—	0.3		
Input leakage current		I_{IN}	$V_{IN} = 0$ to 3.6 V		1.8	—	± 5.0	μA	
3-state output OFF state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	—	± 10.0	μA	
Power-off leakage current		I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	—	± 20.0		

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$) (Note 1)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Min	Max	Unit
			1.8			
Maximum clock frequency	f_{max}	Figure 1, Figure 3	1.8	100	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation delay time (An, Bn-Bn, An)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	3.8	
Propagation delay time (CAB, CBA-Bn, An)	t_{pLH} t_{pHL}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.8	
			3.3 ± 0.3	0.6	4.1	
Propagation delay time (SAB, SBA-Bn, An)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.8	
			3.3 ± 0.3	0.6	4.4	
Output enable time (\overline{OE} , DIR-An, Bn)	t_{pZL} t_{pZH}	Figure 1, Figure 4, Figure 5	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.9	
			3.3 ± 0.3	0.6	4.3	
Output disable time (\overline{OE} , DIR-An, Bn)	t_{pLZ} t_{pHZ}	Figure 1, Figure 4, Figure 5	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	4.3	
Minimum pulse width	t_w (H) t_w (L)	Figure 1, Figure 3	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum setup time	t_s	Figure 1, Figure 3	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t_h	Figure 1, Figure 3	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t_{osLH} t_{osHL}	(Note 2)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics(Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Typ.	Unit
		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note)			
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 2.5 V, V _{IL} = 0 V	(Note)	2.5	0.25	V
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note)	3.3	0.35	
		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note)	1.8	-0.15	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 2.5 V, V _{IL} = 0 V	(Note)	2.5	-0.25	V
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note)	3.3	-0.35	
		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note)	1.8	1.55	V
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 2.5 V, V _{IL} = 0 V	(Note)	2.5	2.05	
		V _{IH} = 3.3 V, V _{IL} = 0 V	(Note)	3.3	2.65	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Typ.	Unit
		(DIR, OE, CAB, CBA, SAB, SBA)	—			
Input capacitance	C _{IN}	(DIR, OE, CAB, CBA, SAB, SBA)	—	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	—	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz	(Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$$

AC Test Circuit

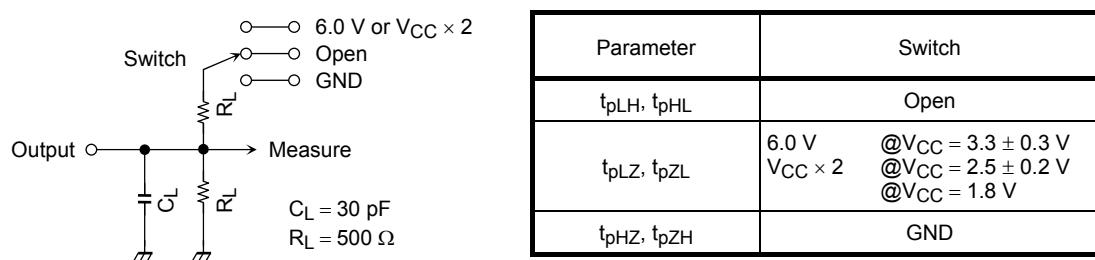
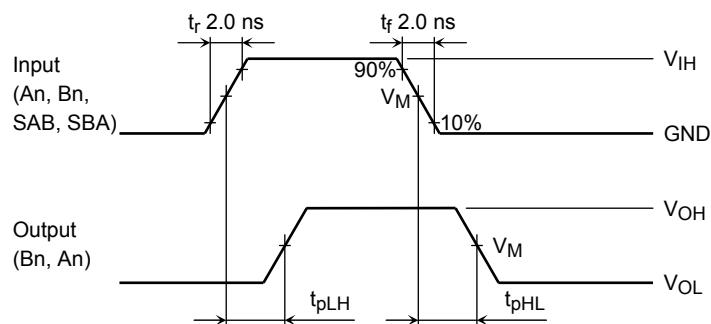
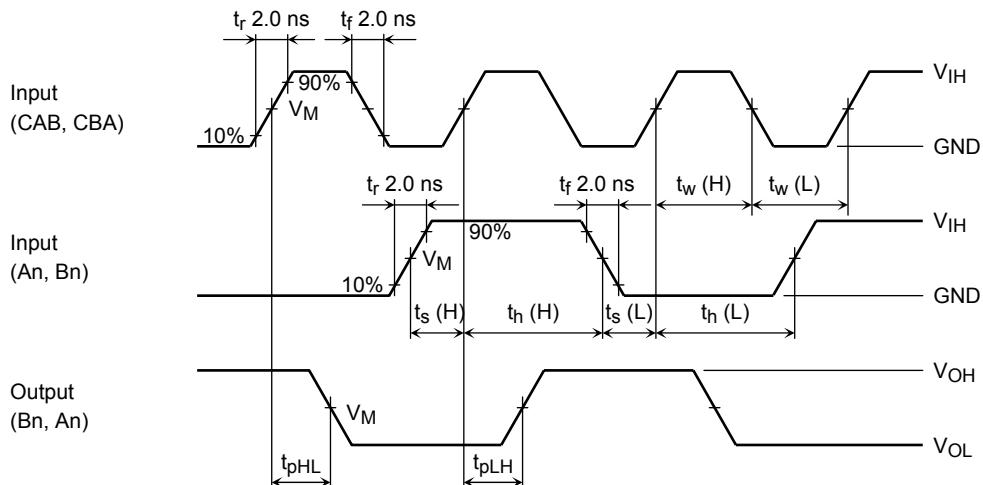
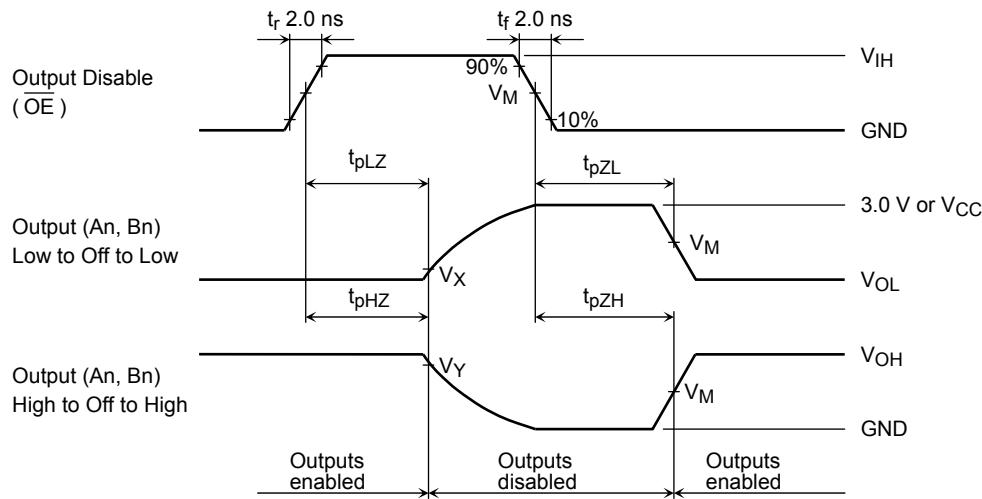
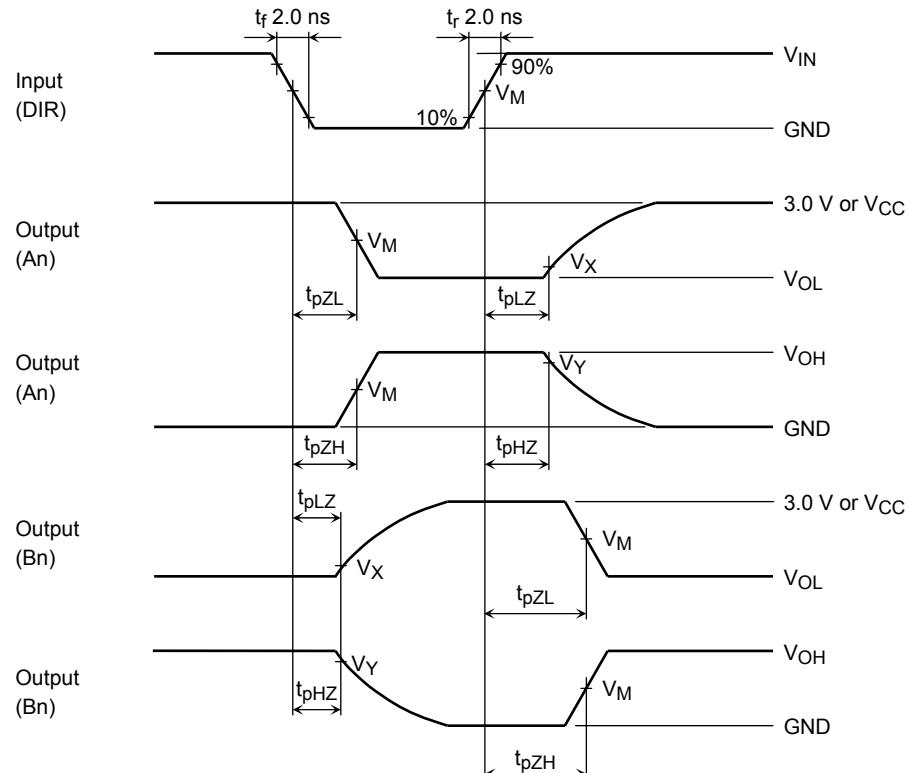


Figure 1

AC Waveform

Figure 2 t_{pLH}, t_{pHL} Figure 3 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

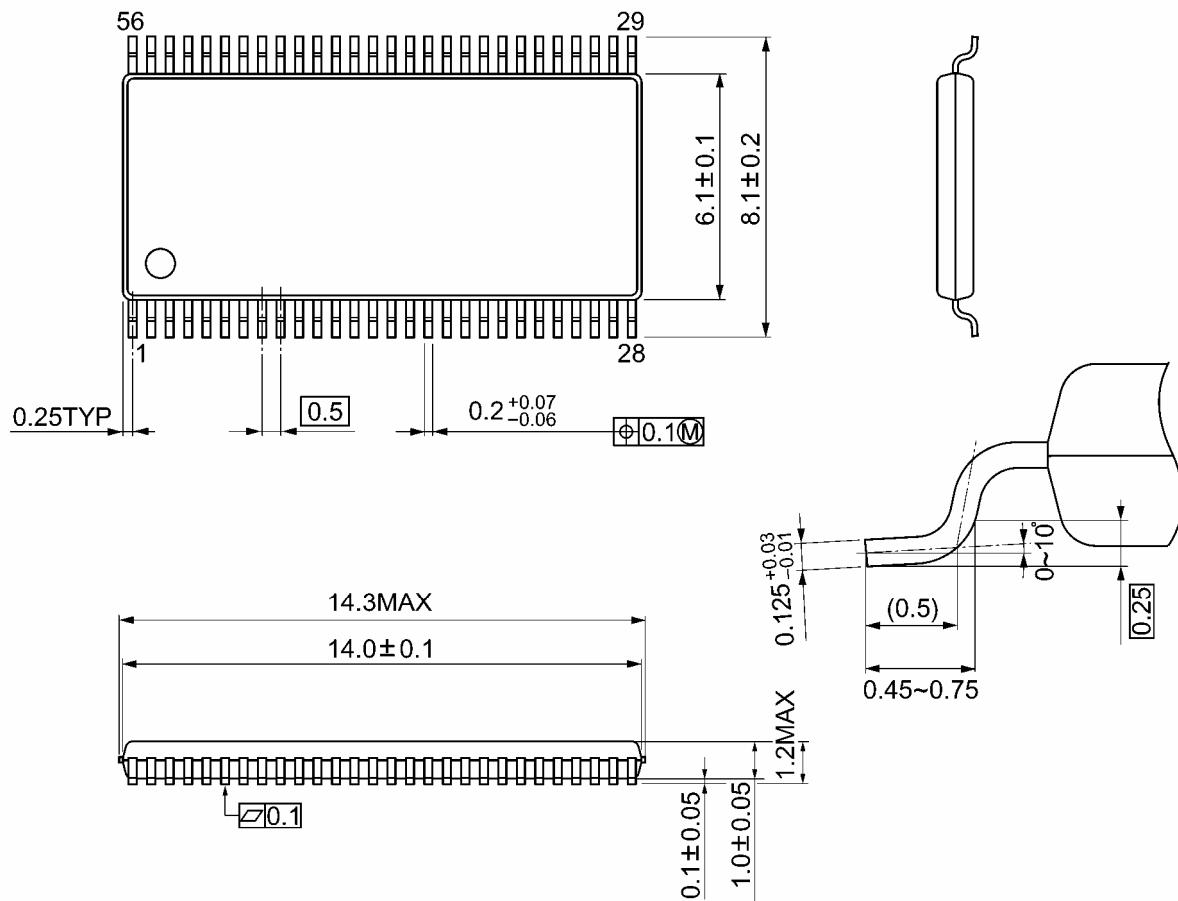
Figure 4 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH} Figure 5 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	$3.3 \pm 0.3\text{ V}$	$2.5 \pm 0.2\text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3\text{ V}$	$V_{OL} + 0.15\text{ V}$	$V_{OL} + 0.15\text{ V}$
V_Y	$V_{OH} - 0.3\text{ V}$	$V_{OH} - 0.15\text{ V}$	$V_{OH} - 0.15\text{ V}$

Package Dimensions

TSSOP56-P-0061-0.50A

Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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